

SCDS248B-OCTOBER 2009-REVISED APRIL 2011

\pm 6 V/+12 V, 5 Ω , LOW r_{ON} SINGLE SPDT ANALOG SWITCH

Check for Samples: TS12A12511

FEATURES

- ±2.7 V to ±6 V Dual Supply
- 2.7 V to 12 V Single Supply
- 5-Ω (typ) ON-State Resistance
- 1.6-Ω (typ) ON-State Resistance Flatness
- 3.3-V, 5-V Compatible Digital Control Inputs
- Rail-to-Rail Analog Signal Handling
- Fast ton, toff Times
- Tiny 8-Lead SOT-23, 8-Lead MSOP, and QFN-8 Packages
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

APPLICATIONS

- Automatic Test Equipment
- Power Routing
- Communication Systems
- Data Acquisition Systems
- Sample-and-Hold Systems
- Relay Replacement
- Battery-Powered Systems



NO – Normally open

The Exposed Thermal Pad must be

electrically connected to V_ or left floating.

DESCRIPTION/ORDERING INFORMATION

The TS12A12511 is a single-pole double-throw (SPDT) analog switch capable of passing signals with swings of 0 to 12 V or –6 V to 6 V. This switch conducts equally well in both directions when it is on. It also offers a low ON-state resistance of 5 Ω (typical), which is matched to within 1 Ω between channels. The max current consumption is <1 μ A and –3 dB bandwidth is >93 MHz. The TS12A12511 exhibits break-before-make switching action, preventing momentary shorting when switching channels. This device is available packaged in an 8-lead MSOP, 8-lead SOT-23, and a 8-pin QFN.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

TS12A12511

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STRUMENTS

EXAS

Table 1. ORDERING INFORMATION

T _A	PACK	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
	MSOP – DGK	Tape and reel	TS12A12511DGKR	2US
–40°C to 85°C	QFN – DRJ	Tape and reel	TS12A12511DRJR	ZVE
	SOT – DCN	Tape and reel	TS12A12511DCNR	NFH

(1) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

	TRUTH TABLE							
IN	NC TO COM, COM TO NC NO TO COM, COM TO							
L	On	Off						
Н	Off	On						

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

 $T_A = 25^{\circ}C$ (unless otherwise noted).

			MIN	MAX	UNIT
V ₊ to V_				13	V
V ₊ to GND)		-0.3	13	V
V_ to GND)		-6.5	0.3	V
V _{I/O}	Analog inputs	V0.5	V ₊ + 0.5	V	
I _{IN}	Digital inputs			±30	mA
	Peak current	NC, NO, or COM		±100	mA
I _{I/O}	Continuous current	NC, NO, or COM		±50	mA
T _{stg}	Storage temperature range		-65	150	°C
T _A	Operating temperature range		-40	85	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL IMPEDANCE RATINGS

				UNIT
		DCN package	220	
θ_{JA}	Package thermal impedance	DGK package	173	°C/W
		DRJ package	103	

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ELECTRICAL CHARACTERISTICS ±5-V Dual Supply

 V_{+} = 5 V \pm 10%, V_{-} = -5 V \pm 10%, T_{A} = -40°C to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T _A = 25°C			T _A = -40°C to 85°C		
FARAMETER	STNIBUL	TEST CONDITIONS	MIN	TYP	МАХ	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range						V_		V+	V
ON-state resistance	r _{ON}	V_{NC} = -4.5 V to +4.5 V or V_{NO} = -4.5 V to 4.5 V, I_{COM} = -10 mA; see Figure 12		5			5	8	Ω
ON-state resistance match between channels	Δr _{ON}			1	1.2			1.6	Ω
ON-state resistance flatness	r _{ON(flat)}	$ \begin{array}{l} V_{NC} = -3.3 \ V \ to \ +3.3 \ V \\ or \ V_{NO} = -3.3 \ V \ to \ +3.3 \ V, \\ I_{COM} = -10 \ mA \end{array} $		1.6	2.2			2.2	Ω
Leakage Currents									
OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	$ \begin{array}{l} V_{NC} = -4.5 \; V \; to \; +4.5 \; V \\ or \; V_{NO} = -4.5 \; V \; to \; +4.5 V \\ V_{COM} = -4.5 \; V \; to \; +4.5 \; V; \; see \; Figure \; 13 \end{array} $		±0.5	±1			±50	nA
ON leakage current	I _{NC(ON)} , I _{NO(ON)}	$ \begin{array}{l} V_{NC} = -4.5 \ V \ to \ +4.5 \ V \\ or \ V_{NO} = -4.5 \ V \ to \ +4.5 \ V \\ V_{COM} = open; \ see \ Figure \ 14 \end{array} $		±0.5	±1			±50	nA
Digital Inputs									
High-level input voltage	V _{INH}					2.4		V+	V
Low-level input voltage	V _{INL}					0		0.8	V
Input current	I _{INL} , I _{INH}	$V_{IN} = V_{INL} \text{ or } V_{INH}$		0.005				±1	μΑ
Control input capacitance	C _{IN}			2.5					pF
Dynamic ⁽¹⁾									
Turn-ON time	t _{ON}	$ \begin{array}{l} R_{L} = 300 \ \Omega, \ C_{L} = 35 \ pF, \\ V_{COM} = 3.3 \ V; \ see \ Figure \ 16 \end{array} $		80	95			115	ns
Turn-OFF time	t _{OFF}	$\begin{array}{l} R_{L} = 300 \ \Omega, \ C_{L} = 35 \ pF, \\ V_{COM} = 3.3 \ V \end{array}$		41	50			56	ns
Break-before-make time delay	t _{BBM}	$\begin{array}{l} R_{L} = 300 \ \Omega, \ C_{L} = 35 \ pF, \\ V_{NC} = V_{NO} = 3.3 \ V; \ see \ Figure \ 17 \end{array}$		36		18			ns
Charge injection	Q _C	$\label{eq:Vnc} \begin{split} V_{NC} = V_{NO} = 0 \ V, \ R_{GEN} = 0 \ \Omega, \ C_L = 1 \ nF; \\ see \ Figure \ 18 \end{split}$		26					рС
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 19		-70					dB
Channel-to-channel crosstalk	X _{TALK}	R_L = 50 $\Omega,~C_L$ = 5 pF, f = 1 MHz, see Figure 20		-70					dB
Bandwidth –3 dB	BW	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 21		93					MHz
Total harmonic distortion	THD	$\label{eq:RL} \begin{array}{l} R_{L} = 600 \ \Omega, \ C_{L} = 15 pF, \ VNO = 1 V_{RMS}, \\ f = 20 \ kHz; \ see \ Figure \ 22 \end{array}$		0.004					%
NC, NO OFF capacitance	$\begin{array}{c} C_{NC(OFF)},\\ C_{NO(OFF)} \end{array}$	f = 1 MHz; see Figure 15		14					pF
COM, NC, NO ON capacitance	$\begin{array}{c} C_{COM(ON)},\\ C_{NC(ON)},\\ C_{NO(ON)} \end{array}$	f = 1 MHz; see Figure 15		60					pF
Supply									
Positive supply current	I+			0.03				1	μA

(1) Ensured by design, not subject to production test.



ELECTRICAL CHARACTERISTICS 12-V Single Supply

V₊ = 12 V ± 10%, V₋ = 0 V, GND = 0 V, T_A = -40° C to 85°C (unless otherwise noted)

				Т _А = 25°С		T _A = -40°C to 85°C			
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	ТҮР	MAX	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range						0		V+	V
ON-state resistance	r _{on}	$\begin{array}{l} V_{NC}=0 \ V \ to \ 10.8 \ V \ or \ V_{NO}=0 \ V \ to \\ 10.8 \ V, \\ I_{COM}=-10 \ mA, \ see \ Figure \ 12 \end{array}$		5			5	8	Ω
ON-state resistance match between channels	Δr _{on}	$\label{eq:VNC} \begin{array}{l} V_{NC}=0 \mbox{ V to } 10.8 \mbox{ V or } V_{NO}=0 \mbox{ V to } \\ 10.8 \mbox{ V,} \\ I_{COM}=-10 \mbox{ mA} \end{array}$		1.6	2.4			2.6	Ω
ON-state resistance flatness	r _{on(flat)}	$$V_{NC}=3.3$ V to 7V or $V_{NO}=3.3$ V to 7 V, $$I_{COM}=-10$ mA$		1.7			1.8	3.2	Ω
Leakage Currents					·			·	
OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	$ \begin{array}{l} V_{NC} = 0 \; V \; to \; 10.8 \; V \; or \; V_{NO} = 0 \; V \; to \\ 10.8 \; V, \\ V_{COM} = 0 \; V \; to \; 10.8 \; V; \; see \\ Figure \; 13 \end{array} $		±0.5	±10			±50	nA
ON leakage current	I _{NC(ON)} , I _{NO(ON)}	V_{NC} = 0 V to 10.8V or V_{NO} = 0 V to 10.8 V, V_{COM} = open; see Figure 14		±0.5	±10			±50	nA
Digital Inputs					·			·	
High-level input voltage	V _{INH}					5		V+	V
Low-level input voltage	V _{INL}					0		0.8	V
Input current	I _{INL} , I _{INH}	$V_{IN} = V_{INL}$ or V_{INH}		±0.005				±0.1	μA
Digital input capacitance	CIN			2.7					pF

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ELECTRICAL CHARACTERISTICS 12-V Single Supply (continued)

$V_{+} = 12 V \pm 10\%, V_{-} =$	0 V, GND = 0 V	/, $T_A = -40^{\circ}C$ to $85^{\circ}C$ (u	unless otherwise noted)

DADAMETER		TEAT CONDITIONS	T _A = 25°C			T _A = −40°C to 85°C			
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	ТҮР	MAX	MIN	TYP	MAX	UNIT
Dynamic ⁽¹⁾									
Turn-ON time	t _{ON}	$ \begin{array}{l} R_{L} = 300 \; \Omega, C_{L} = 35 \; pF, \\ V_{COM} = 3.3 \; V; see \; Figure \; 16 \end{array} $		56	85			110	ns
Turn-OFF time	t _{OFF}	$\label{eq:relation} \begin{array}{l} R_{L} = 300 \ \Omega, \ C_{L} = 35 \ pF, \\ V_{COM} = 3.3 \ V; \ see \ Figure \ 16 \end{array}$		25	30			31	ns
Break-before-make time delay	t _{BBM}			30		19			ns
Charge injection	Q _C	$\begin{array}{l} R_{GEN}=V_{NC}=V_{NO}=0 \ V, \ R_{GEN}=0 \\ \Omega, \ C_{L}=1 \ nF; \\ \text{see Figure 18} \end{array}$		491					рС
OFF isolation	O _{ISO}	$\label{eq:RL} \begin{array}{l} R_{L} = 50 \ \Omega, \ C_{L} = 5 \ pF, \ f = 1 \ MHz, \\ see \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $		-70					dB
Channel-to-channel crosstalk	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 20		-70					dB
Bandwidth –3 dB	BW	$R_L = 50 \Omega$, $C_L = 5 pF$, see Figure 21		122					MHz
Total harmonic distortion	THD	R_L = 600 Ω, C_L = 15pF, V_{NO} = 1 V_{RMS} , f = 20 kHz; see Figure 22		0.04					%
NC, NO OFF capacitance	C _{NC(OFF)} , CI _{NO(OFF)}	f = 1 MHz, see Figure 15		14					pF
COM, NC, NO ON capacitance	$C_{COM(ON)}, C_{NC(ON)}, C_{NO(ON)}$	f = 1 MHz, see Figure 15		55					pF
Supply									
Positive supply current	I+			0.07				1	μA

(1) Ensured by design, not subject to production test.



ELECTRICAL CHARACTERISTICS 5-V Single Supply

V₊ = 5 V ± 10%, V₋ = 0 V, GND = 0 V, T_A = -40° C to 85°C (unless otherwise noted)

DADAMETED	OVMDOL	TEST CONDITIONS	T _A = 25°C			T _A = -40°C to 85°C			UNIT
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Analog Switch									
Analog signal range						0		V+	V
ON-state resistance	r _{on}	$ \begin{array}{l} V_{NC} = 0 \ V \ to \ 4.5 \ V \ or \ V_{NO} = 0 \ V \ to \\ 4.5 \ V, \\ I_{COM} = -10 \ mA; \\ see \ Figure \ 12 \end{array} $		8	10			12.5	Ω
ON-state resistance match between channels	Δr_{on}	$V_{\rm NC}$ =0 V to 4.5 V or $V_{\rm NO}$ = 0 V to 4.5 V, $I_{\rm COM}$ = –10 mA		1	1.1			1.5	Ω
ON-state resistance flatness	r _{on(flat)}	$V_{\rm NC}$ =0 V to 4.5 V or $V_{\rm NO}$ = 0 V to 4.5 V, $I_{\rm COM}$ = –10 mA		1.3			1.3	2	Ω
Leakage Currents								ŧ	
OFF leakage current	I _{NC(OFF)} , I _{NO(OFF)}	$ \begin{array}{l} V_{NC} = 0 \ V \ to \ 4.5 \ V \ or \ V_{NO} = 0 \ V \ to \\ 4.5 \ V, \\ V_{COM} = 0 \ V \ to \ 4.5 \ V; \ see \ Figure \ 13 \end{array} $		±0.5	±1			±50	nA
ON leakage current	I _{NC(ON)} , I _{NO(ON)}			±0.5	±1			±50	nA
Digital Inputs									
High-level input voltage	V _{INH}					2.4		V+	V
Low-level input voltage	V _{INL}					0		0.8	V
Input current	I _{INL} , I _{INH}	$V_{IN} = V_{INL}$ or V_{INH}		0.01				±0.1	μA
Digital input capacitance	C _{IN}			2.8					pF

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ELECTRICAL CHARACTERISTICS 5-V Single Supply (continued)

$V_{+} = 5 V \pm 10\%, V_{-} = 0 V$, GND = 0 V, $T_A = -$	-40°C to 85°C (unless	s otherwise noted)
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	0/450	TEAT CONDITIONS	T _A = 25°C			T _A = -4			
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
Dynamic ⁽¹⁾	•	-							
Turn-ON time	t _{ON}	R_L = 300 Ω, C_L = 35 pF, V _{COM} = 3.3 V; see Figure 16		119	145			178	ns
Turn-OFF time	t _{OFF}	R_L = 300 Ω, C_L = 35 pF, V _{COM} = 3.3 V; see Figure 16		38	47			95.2	ns
Break-before-make time delay	t _{BBM}			79		44			ns
Charge injection	Q _C	$\begin{array}{l} V_{GEN}=V_{NC}=V_{NO}=0~V,~R_{GEN}=0\\ \Omega,~C_L=1~nF;\\ see~Figure~18 \end{array}$		65					рС
OFF isolation	O _{ISO}	$\label{eq:RL} \begin{array}{l} R_{L} = 50 \ \Omega, \ C_{L} = 5 \ pF, \ f = 1 \ MHz, \\ see \ Figure \ 19 \end{array}$		-70					dB
Channel-to-channel crosstalk	X _{TALK}	$\label{eq:RL} \begin{array}{l} R_{L} = 50 \ \Omega, \ C_{L} = 5 \ pF, \ f = 1 \ MHz, \\ see \ Figure \ 20 \end{array}$		-70					dB
Bandwidth –3 dB	BW	$R_L = 50 \Omega$, see Figure 21		152					MHz
Total harmonic distortion	THD	$ \begin{array}{l} R_{L} = 600 \ \Omega, \ C_{L} = 15 \ pF, \ V_{NO} = 1 \\ VRMS, \ f = 20 \ kHz; \ see \ \textbf{Figure} \ \textbf{22} \end{array} $		0.04					%
NC, NO OFF capacitance	$\begin{array}{c} C_{\text{NC(OFF)}},\\ C_{\text{NO(OFF)}} \end{array}$	f = 1 MHz, see Figure 15		15					pF
COM, NC, NO ON capacitance	$\begin{array}{c} C_{COM(ON)},\\ C_{NC(ON)},\\ I_{NO(ON)} \end{array}$	f = 1 MHz, see Figure 15		55					pF
Power Requirements									
V ₊ supply current	I+	$V_{IN} = 0 \vee \text{or } V_{+}$		0.02				1	μA

(1) Ensured by design, not subject to production test.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

Pin Function Descriptions

TERMINAL		DESCRIPTION					
NAME	NO.	DESCRIPTION					
1	COM	Common terminal. Can be an input or output.					
2	NC	Normally closed. Can be an input or output.					
3	GND	Ground (0 V) reference					
4	V+	Most positive power supply					
5	N.C.	No connect. Not internally connected.					
6	IN	Logic control input					
7	V_	Most negative power supply. This pin is only used in dual-supply applications and should be tied to ground in single-supply applications.					
8	NO	Normally open. Can be an input or output.					



Figure 3. Leakage Current vs I/O Voltage (Switch OFF)

0.0

Switch I/O Voltage (V)

2.0

4.0

6.0

0.50

0.00

-40.00

-4.0

-2.0

-6.0





25.00

85.00



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6.0

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Figure 11. Charge Injection vs Bias Voltage



TEST CIRCUITS



Figure 12. ON-State Resistance



Figure 13. OFF-State Leakage Current (I_{COM(OFF)}, I_{NC(OFF)})



Figure 14. ON-State Leakage Current (I_{COM(ON)}, I_{NC(ON)})

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Figure 15. Capacitance (C_{COM(OFF)}, C_{COM(ON)}, C_{NC(OFF)}, C_{NC(ON)})



⁽¹⁾ All input pulses are supplied by generators having the following characteristics: PRPs 10 MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns. ⁽²⁾ C_L includes probe and jig capacitance.

Figure 16. Turn-ON (t_{ON}) and Turn-OFF Time (t_{OFF})



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⁽¹⁾ All input pulses are supplied by generators having the following characteristics: PRFs 10 MHz, $Z_0 = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns. ⁽²⁾ C_L includes probe and jig capacitance.



Figure 17. Break-Before-Make Time Delay (t_{BBM})

 $^{(1)}$ C_L includes probe and jig capacitance.

⁽²⁾ All input pulses are supplied by generators having the following characteristics: PRR 10 MHz, $Z_0 = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.

Figure 18. Charge Injection (Q_C)



Figure 19. OFF Isolation (O_{ISO})

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Figure 21. Bandwidth (BW)



 $^{(1)}$ C_L includes probe and jig capacitance.





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REVISION HISTORY

Changes from Revision A (May 2010) to Revision B					
•	Deleted preview status from DGK and DCN packages.	1			

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION

REEL DIMENSIONS

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TAPE AND REEL INFORMATION

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TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS12A12511DCNR	SOT-23	DCN	8	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
TS12A12511DGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS12A12511DRJR	SON	DRJ	8	1000	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

16-Aug-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS12A12511DCNR	SOT-23	DCN	8	3000	202.0	201.0	28.0
TS12A12511DGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0
TS12A12511DRJR	SON	DRJ	8	1000	210.0	185.0	35.0

DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.

- D Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
- E. Falls within JEDEC MO-187 variation AA, except interlead flash.



DCN (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



- A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.
- C. Package outline exclusive of metal burr & dambar protrusion/intrusion.
- D. Package outline inclusive of solder plating.
- E. A visual index feature must be located within the Pin 1 index area.
- F. Falls within JEDEC MO-178 Variation BA.
- G. Body dimensions do not include flash or protrusion. Mold flash and protrusion shall not exceed 0.25 per side.





- NOTES: A. All linear dimensions are in millimeters. В. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers D. should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA



C. SON (Small Outline No-Lead) package configuration.

The package thermal pad must be soldered to the board for thermal and mechanical performance. See the Product Data Sheet for details regarding the exposed thermal pad dimensions.

E. Package complies to JEDEC MO-229 variation WGGB.





THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: All linear dimensions are in millimeters



DRJ (S-PWSON-N8)

SMALL PACKAGE OUTLINE NO-LEAD



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>.
- E. Laser cutting apertures with electropolish and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for solder mask tolerances and vias tenting recommendations for vias placed in the thermal pad.



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